



FAST CMOS OCTAL BUFFER/LINE DRIVER

IDT74FCT541A/C

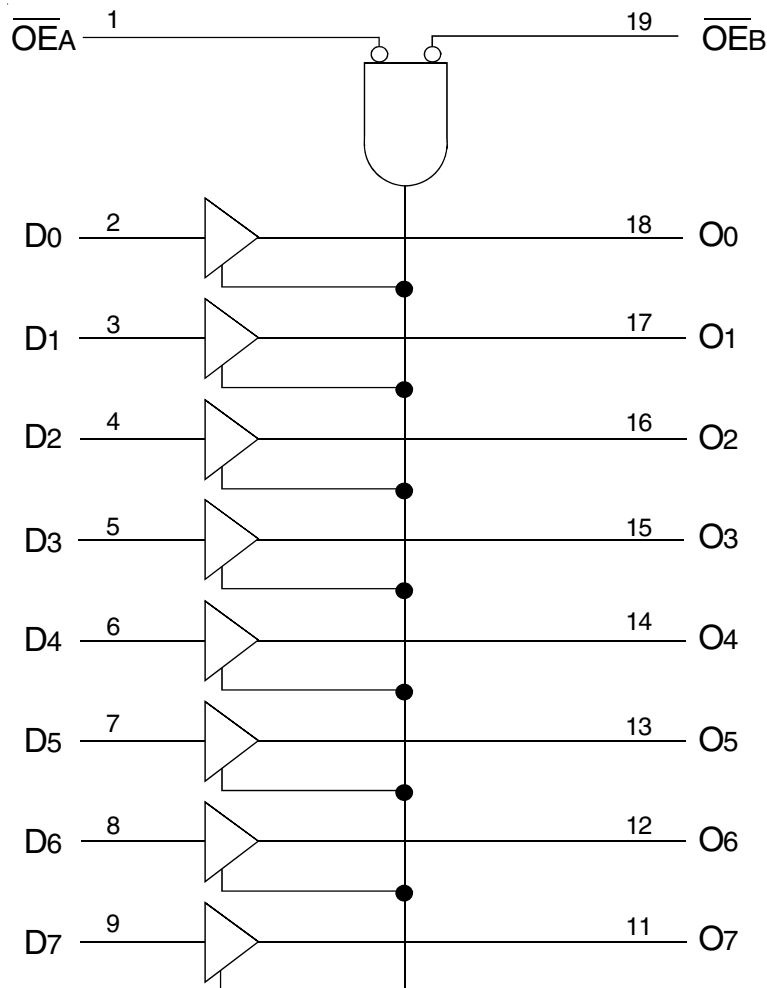
FEATURES:

- IDT74FCT541A up to 25% faster than FAST
- IDT74FCT541C up to 55% faster than FAST
- $I_{OL} = 64\text{mA}$
- CMOS power levels (1mW typ. static)
- Meets or exceeds JEDEC Standard 18 specifications
- Available in SOIC package

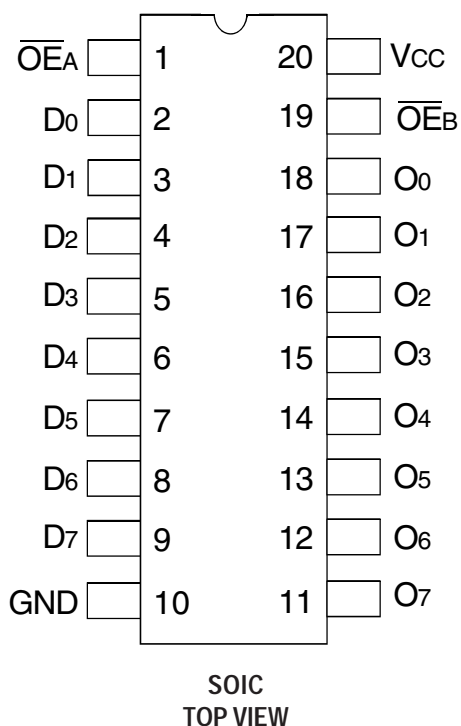
DESCRIPTION:

The IDT octal buffer/line drivers are built using an advanced dual metal CMOS technology. The FCT541 is designed to be employed as a memory and address driver, clock driver and bus-oriented transmitter/receiver which provides improved board density. The FCT541 is similar in function to the FCT244, except that the inputs and outputs are on opposite sides of the package. This pinout arrangement makes these devices especially useful as output ports for microprocessors and as backplane drivers, allowing ease of layout and greater board density.

FUNCTIONAL BLOCK DIAGRAM



PIN CONFIGURATION



ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Rating	Commercial	Military	Unit
V _{TERM} ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7	-0.5 to +7	V
V _{TERM} ⁽³⁾	Terminal Voltage with Respect to GND	-0.5 to V _{CC}	-0.5 to V _{CC}	V
T _A	Operating Temperature	0 to +70	-55 to +125	°C
T _{BIAS}	Temperature under BIAS	-55 to +125	-65 to +135	°C
T _{STG}	Storage Temperature	-55 to +125	-65 to +150	°C
P _T	Power Dissipation	0.5	0.5	W
I _{OUT}	DC Output Current	120	120	mA

NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability. No terminal voltage may exceed V_{CC} by +0.5V unless otherwise noted.
- Input and V_{CC} terminals only.
- Output and I/O terminals only.

CAPACITANCE (T_A = +25°C, F = 1.0MHz)

Symbol	Parameter ⁽¹⁾	Conditions	Typ.	Max.	Unit
C _{IN}	Input Capacitance	V _{IN} = 0V	6	10	pF
C _{OUT}	Output Capacitance	V _{OUT} = 0V	8	12	pF

NOTE:

- This parameter is measured at characterization but not tested.

PIN DESCRIPTION

Pin Names	Description
\overline{OE}_A , \overline{OE}_B	3-State Output Enable Inputs (Active LOW)
D _x	Inputs
O _x	Outputs

FUNCTION TABLE⁽¹⁾

Inputs			Output
\overline{OE}_A	\overline{OE}_B	D _x	O _x
L	L	L	L
L	L	H	H
H	H	X	Z

NOTE:

- H = HIGH Voltage Level
X = Don't Care
L = LOW Voltage Level
Z = High Impedance

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

Following Conditions Apply Unless Otherwise Specified: $V_{LC} = 0.2V$; $V_{HC} = V_{CC} - 0.2V$

Commercial: $T_A = 0^\circ C$ to $+70^\circ C$, $V_{CC} = 5.0V \pm 5\%$

Symbol	Parameter	Test Conditions ⁽¹⁾		Min.	Typ. ⁽²⁾	Max.	Unit
V_{IH}	Input HIGH Level	Guaranteed Logic HIGH Level		2	—	—	V
V_{IL}	Input LOW Level	Guaranteed Logic LOW Level		—	—	0.8	V
I_{IH}	Input HIGH Current	$V_{CC} = \text{Max.}$	$V_i = V_{CC}$	—	—	5	μA
I_{IL}	Input LOW Current		$V_i = 2.7V$	—	—	5 ⁽⁴⁾	
			$V_i = 0.5V$	—	—	-5 ⁽⁴⁾	
I_{OZH}	Off State (High Impedance) Output Current	$V_{CC} = \text{Max.}$	$V_o = V_{CC}$	—	—	10	μA
			$V_o = 2.7V$	—	—	10 ⁽⁴⁾	
			$V_o = 0.5V$	—	—	-10 ⁽⁴⁾	
			$V_o = GND$	—	—	-10	
V_{IK}	Clamp Diode Voltage	$V_{CC} = \text{Min.}, I_{IN} = -18mA$		—	-0.7	-1.2	V
I_{OS}	Short Circuit Current	$V_{CC} = \text{Max.}, V_o = GND^{(3)}$		-60	-120	—	mA
V_{OH}	Output HIGH Voltage	$V_{CC} = 3V, V_{IN} = V_{LC} \text{ or } V_{HC}, I_{OH} = -32\mu A$		V_{HC}	V_{CC}	—	V
		$V_{CC} = \text{Min}$	$I_{OH} = -300\mu A$	V_{HC}	V_{CC}	—	
		$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -15mA$	2.4	4.3	—	
V_{OL}	Output LOW Voltage	$V_{CC} = 3V, V_{IN} = V_{LC} \text{ or } V_{HC}, I_{OL} = 300\mu A$		—	GND	V_{LC}	V
		$V_{CC} = \text{Min}$	$I_{OL} = 300\mu A$	—	GND	$V_{LC}^{(4)}$	
		$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 64mA$	—	0.3	0.55	

NOTES:

1. For conditions shown as Min. or Max., use appropriate value specified under Electrical Characteristics for the applicable device type.
2. Typical values are at $V_{CC} = 5.0V$, $+25^\circ C$ ambient and maximum loading.
3. Not more than one output should be tested at one time. Duration of the test should not exceed one second.
4. This parameter is guaranteed but not tested.

POWER SUPPLY CHARACTERISTICS

$V_{LC} = 0.2V$; $V_{HC} = V_{CC} - 0.2V$

Symbol	Parameter	Test Conditions ⁽¹⁾		Min.	Typ. ⁽²⁾	Max.	Unit
I _{CC}	Quiescent Power Supply Current	$V_{CC} = \text{Max.}$ $V_{IN} \geq V_{HC}$; $V_{IN} \leq V_{LC}$		—	0.2	1.5	mA
ΔI_{CC}	Quiescent Power Supply Current TTL Inputs HIGH	$V_{CC} = \text{Max.}$ $V_{IN} = 3.4V^{(3)}$		—	0.5	2	mA
I _{CCD}	Dynamic Power Supply Current ⁽⁴⁾	$V_{CC} = \text{Max.}$ Outputs Open $\overline{OE}_A = \overline{OE}_B = \text{GND}$ or $\overline{OE}_A = \text{GND}$ One Input Toggling 50% Duty Cycle	$V_{IN} \geq V_{HC}$ $V_{IN} \leq V_{LC}$	—	0.15	0.25	mA/ MHz
I _C	Total Power Supply Current ⁽⁶⁾	$V_{CC} = \text{Max.}$ Outputs Open $f_i = 10\text{MHz}$ 50% Duty Cycle $\overline{OE}_A = \overline{OE}_B = \text{GND}$ or $\overline{OE}_A = \text{GND}$ One Bit Toggling	$V_{IN} \geq V_{HC}$ $V_{IN} \leq V_{LC}$ (FCT)	—	1.7	4	mA
			$V_{IN} = 3.4V$ $V_{IN} = \text{GND}$	—	2	5	
		$V_{CC} = \text{Max.}$ Outputs Open $f_i = 2.5\text{MHz}$ 50% Duty Cycle $\overline{OE}_A = \overline{OE}_B = \text{GND}$ or $\overline{OE}_A = \text{GND}$ Eight Bits Toggling	$V_{IN} \geq V_{HC}$ $V_{IN} \leq V_{LC}$ (FCT)	—	3.2	6.5 ⁽⁵⁾	
			$V_{IN} = 3.4V$ $V_{IN} = \text{GND}$	—	5.2	14.5 ⁽⁵⁾	

NOTES:

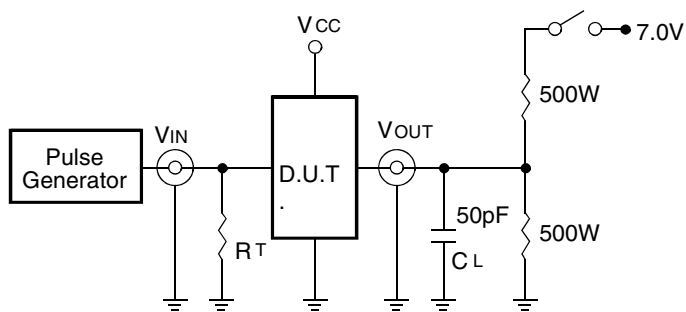
- For conditions shown as Min. or Max., use appropriate value specified under Electrical Characteristics for the applicable device type.
- Typical values are at $V_{CC} = 5.0V$, $+25^\circ\text{C}$ ambient.
- Per TTL driven input; ($V_{IN} = 3.4V$). All other inputs at V_{CC} or GND.
- This parameter is not directly testable, but is derived for use in Total Power Supply Calculations.
- Values for these conditions are examples of ΔI_{CC} formula. These limits are guaranteed but not tested.
- $I_C = I_{QUIESCENT} + I_{INPUTS} + I_{DYNAMIC}$
 $I_C = I_{CC} + \Delta I_{CC} D_H N_T + I_{CCD} (f_{CP}/2 + f_i N_i)$
 $I_{CC} = \text{Quiescent Current}$
 $\Delta I_{CC} = \text{Power Supply Current for a TTL High Input } (V_{IN} = 3.4V)$
 $D_H = \text{Duty Cycle for TTL Inputs High}$
 $N_T = \text{Number of TTL Inputs at } D_H$
 $I_{CCD} = \text{Dynamic Current caused by an Input Transition Pair (HLH or LHL)}$
 $f_{CP} = \text{Clock Frequency for Register Devices (Zero for Non-Register Devices)}$
 $f_i = \text{Output Frequency}$
 $N_i = \text{Number of Outputs at } f_i$

All currents are in milliamps and all frequencies are in megahertz.

SWITCHING CHARACTERISTICS OVER OPERATING RANGE

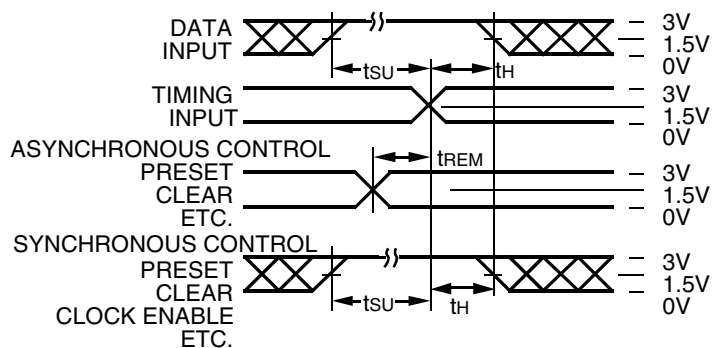
Symbol	Parameter	Condition ⁽¹⁾	74FCT541A		74FCT541C		Unit
			Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	
t_{PLH}	Propagation Delay	$C_L = 50\text{pF}$ $R_L = 500\Omega$	1.5	4.8	1.5	4.1	ns
t_{PHL}	Dx to Ox						
t_{PZH}	Output Enable Time		1.5	6.2	1.5	5.8	ns
t_{PZL}							
t_{PHZ}	Output Disable Time	1.5	5.6	1.5	5.2	ns	
t_{PLZ}							

TEST CIRCUITS AND WAVEFORMS



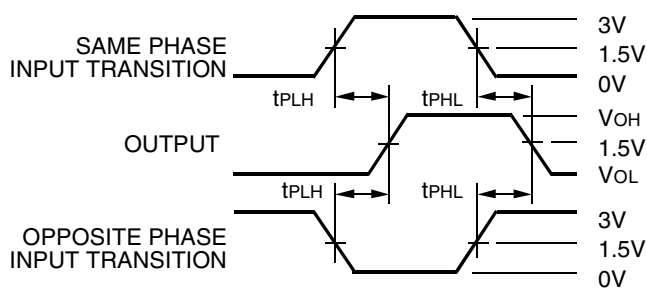
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Test Circuits for All Outputs



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Set-Up, Hold, and Release Times



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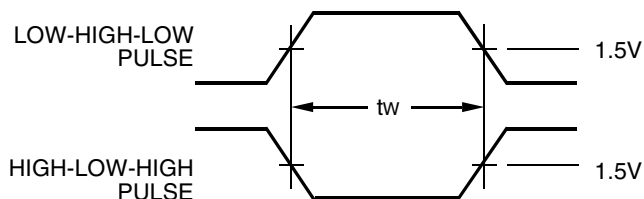
Propagation Delay

SWITCH POSITION

Test	Switch
Open Drain Disable Low Enable Low	Closed
All Other Tests	Open

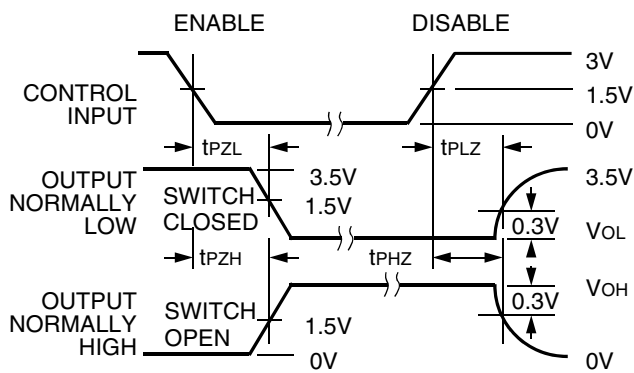
DEFINITIONS:

CL = Load capacitance: includes jig and probe capacitance.
RT = Termination resistance: should be equal to ZOUT of the Pulse Generator.



Pulse Width

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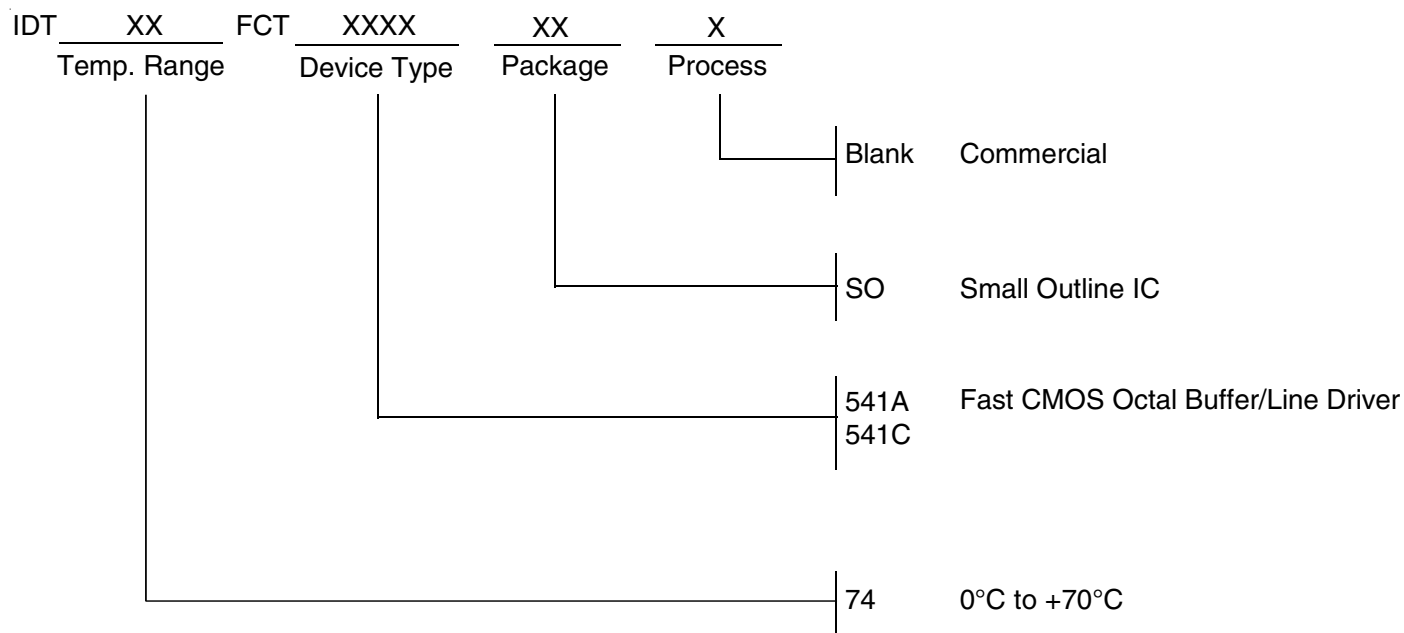
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Enable and Disable Times

NOTES:

- Diagram shown for input Control Enable-LOW and input Control Disable-HIGH.
- Pulse Generator for All Pulses: Rate $\leq 1.0\text{MHz}$; $Z_o \leq 50\Omega$; $t_r \leq 2.5\text{ns}$; $t_f \leq 2.5\text{ns}$.

ORDERING INFORMATION



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